TA8512AF

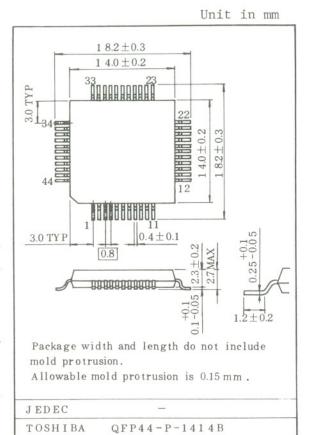
TOSHIBA BIPOLAR INTEGRATED CIRCUIT
SILICON MONOLITHIC

READ/WRITE IC (For Floppy Disk Drive)

TA8512AF is a bipolar monolithic developed for R/W IC for 3~8 inch floppy disk drive.

The read circuit and write circuit and various control circuits for the floppy disk drive are integrated on one chip to realize small size and low power dissipation.

- . To decrease the power dissipation when it is not operated the system has a power save function (The state where read, write, and erase are not performed), and the power dissipation under power save state is 9mW(Typ.)(at 5V single power supply use).
- . The system operates by dual power supples of $V_{CC} = 12V\pm10\% \text{ and } V_{DD} = 5V\pm10\% \text{ or single power supply of } V_{CC} = V_{DD} = 5V\pm10\%.$
- . As a read/write change-over diode switch is built in, the read amplifier differential voltage gain can be set either 100 times or 200 times by the gain select terminals.



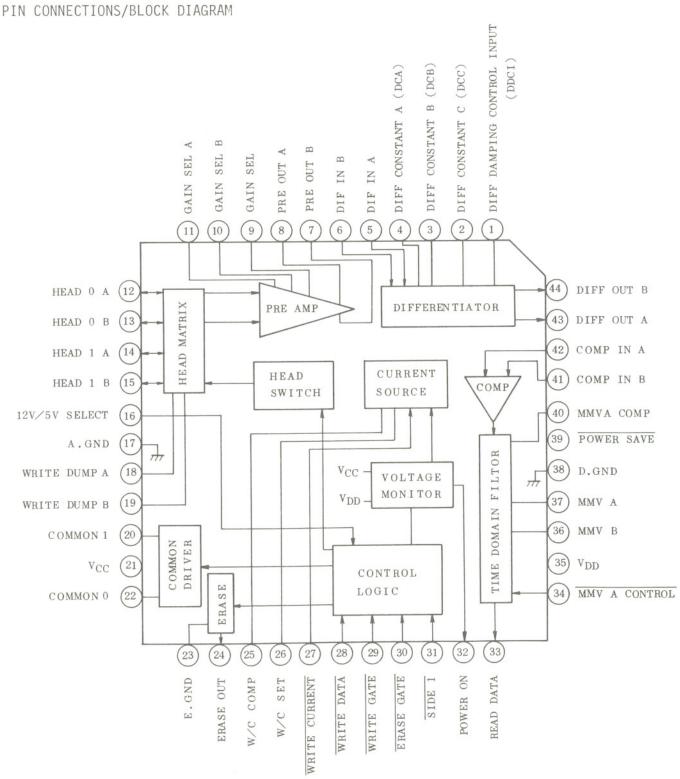
Weight: 1.2g

- . The write current can be optionally set by an external resistance 60 25mADC.
- . As the write current change-over circuit is built in, the current value can be changed-over either internal or external circumference of the disk.
- . The read circuit, write circuit, and erase circuit are incorporated in a chip and control can be make in independent timing by $\overline{\text{WG}}$ and $\overline{\text{EG}}$.
- . The power supply monitoring circuit is incorporated to inhibit abnormal writing at the rise of power supply and occurrence of abnormal power.
- . A capacitor for time domain filter's time constant is incorporated and the time constant can be set by an external resistance.
- . As the time domain filter's time c-nstant changed-over circuit is built in, the period (t1) of the first one shot can be change-over either internal or circumfrence of the disk.
- . As the differentiator component change-over circuit is incorporated, the frequency characteristic of the differentiator can be changed-over.

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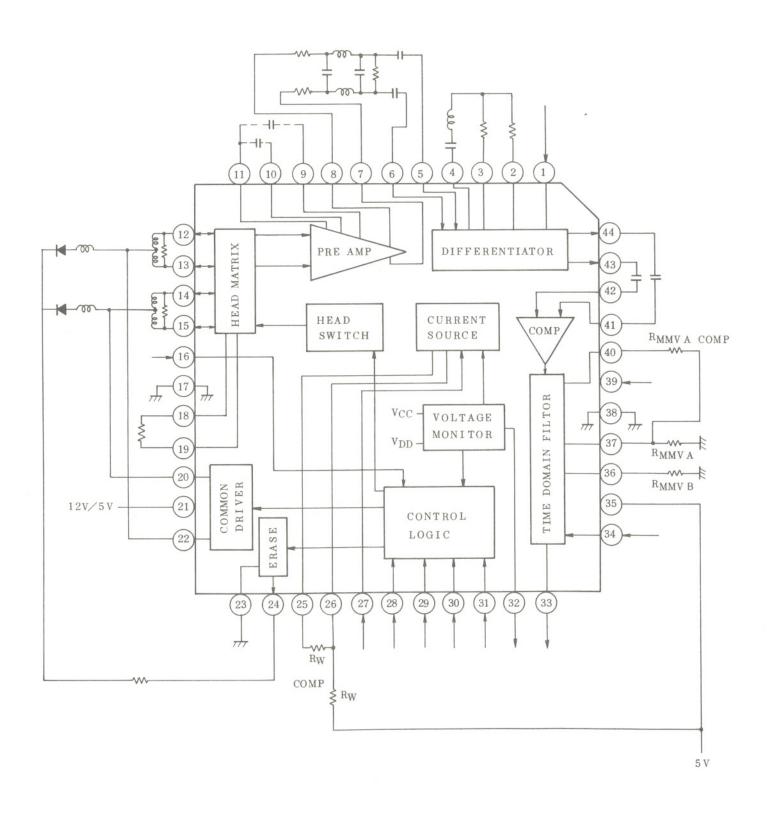
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Please not that 9, 11, 12, 13, 15 pin is not endurable enough against ESD. $(\sim \pm 100 \text{V})$

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TYPICAL APPLICATION



PIN No.	NAME	DESCRIPTION
1	DIFF DAMPING	Active Differentiator Components Select:
	CONTROL INPUT	When logical voltage "L" is input, component between 3 and
		4 terminal and at logical voltage "H", between 2 and 4
		terminal is selected.
2	DIFF CONSTANT C	Active Differentiator Components:
3	DIFF CONSTANT B	Active differentiator components are connected between 4 and
4	DIFF CONSTANT A	2 terminal or between 4 and 3.
5	DIFF IN A	Active Differentiator Inputs:
6	DIFF IN B	From the two preamplifier output terminals, the read signal
		is differentially input through the filter circuit.
7	PRE OUT B	Preamplifier Outputs:
8	PRE OUT A	From the tow terminals, the read signal is differentially
		input to the differentiator input terminals through the
		filter circuit.
9	GAIN SEL	Preamplifier Gain Selects:
10	GAIN SEL B	By AC coupling short between terminal 9 and 11, preamplifier
11	GAIN SEL A	gain of 200 times, and by AC coupling short between terminal
		10 and 11, preamplifier gain of 100 times can be selected.
12	HEAD O A	Head O Connects:
13	HEAD O B	A magnetic head for record/regeneration having a center tap
		and a head damping resistance at the read mode is connected.
14	HEAD 1 A	Head 1 Connects:
15	HEAD 1 B	These are another input/output terminals of one more
		magnetic head the similar as above.
16	12V/5V SELECT	V _{CC} Power Supply Select:
		When logical "L" is input, the mode of V _{CC} =5V use is
		selected.
17	A • GND	Analog Ground
18	WRITE DUMP A	Write Damping Resistance Connects:
19	WRITE DUMP B	Between these terminals a head damping resistance is
		connected at the write mode.

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PIN No.	NAME	DESCRIPTION
20	COMMON 1	Cneter Tap 1:
		This terminal is connected to the center tap of the magnetic
		head 1 and sets the read/write voltage of the head 1.
21	VCC	+12V or +5V Power Supply
22	COMMON 0	Center Tap 0:
		This terminal is connected to the center tap of the
		magnetic head 0 and sets the read/write voltage of the
		head 0.
23	E•GND	Erase Ground
24	ERASE OUTPUT	Erase Current Output:
		This is the open collector terminal for performing sink of
		earsing current.
25	W/C COMP	RW COMP Connect:
		Between this terminal and 26 terminal, the RW COMP is
		connected and sets the increasing write current value.
		(Formula) $I_{WC} = \frac{1.3 - V_{WC}}{RW COMP (\Omega)} \times 10 (ADC)$
26	W/C SET	RW Connect:
		Between this terminal and 35 terminal, the RW is connected
		and sets the write current value.
		(Formula) $I_W = \frac{1.3}{R_W(\Omega)} \times 10 \text{ (ADC)}$
27	WRITE CURRENT	WRITE CURRENT Input:
		At the time of the logical voltage "L" inputs, the write
		current is determined by the sum of IW and IWC, and at
		logical voltage "H", the write current is IW only.
28	WRITE DATA	WRITE DATA Input:
		This is the WRITE DATA input terminal, and triggered at
		digital input H→L.
29	WRITE GATE	WRITE GATE Input:
		This is a pull up terminal which becomes the write system
		active by the input of the logical voltage "L".

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PIN No.	NAME	DESCRIPTION
30	ERASE GATE	ERASE GATE Input:
		This is a pull up terminal which becomes the erase system
		active by the input of the logical voltage "L".
31	SIDE 1	SIDE 1 Input:
		This is a pull up terminal, and at the input of the logical
		voltage "L" the Head 1 system becomes active, and at the
		input of the logical voltage "H", the Head O system becomes
		active.
32	POWER ON	Power On Output:
		This is the open collector terminal which outputs "L" when
		at least either one of power supply VDD and VCC is less
		than the specified value.
33	READ DATA	Read Data Output:
	,	From this terminal digital signal (Read Data) outputs.
34	MMVA CONTROL	MMVA CONTROL Input:
		When logical voltage "L" inputs, the period (t1) of the
		one-shot time becomes narrow.
35	$V_{ m DD}$	+5V Power Supply
36	MMVB	RMMVB Connect:
		This terminal is connected with the period (t2) of the
		one-shot time setting resistance RMMVB.
		The period of the second one-shot time is determined by
		$t2=27 \times (R_{MMVB} (\Omega) + 100) \times 10^{-12} (ns)$
37	MMVA	R _{MMVA} Connect:
		This terminal is connected with the period (t1) of the
		one-shot time setting resistance RMMVA.
		The period of the first one-shot time is determined by $t1=53.5 \times (R_{MMVA} (\Omega) + 100) \times 10^{-12}$ (ns)
		Note: Setting of RA=RMMVA when logical voltage
		"H" inputs to MMVA CONTROL. When logical voltage "L"
		inputs to MMVA CONTROL, RA=RMMVA// RMMVA COMP and
1		I AMATAA

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PIN No.	NAME	DESCRIPTION
38	D•GND	Digital Ground
39	POWER SAVE	POWER SAVE Input:
		When logical voltage "L" inputs to POWER SAVE, reduces the
		power dissipation of R/W IC (at the power save mode).
		During the power save mode, read, write, and erase are not
		carried out.
		(Power supply monitor circuit is operating.)
40	MMVA COMP	RMMVA COMP Connect:
		This is an open collector terminal for connecting the
		corrected period (t1) of one-shot time setting resistance
		R _{MMVA} COMP to the terminal 37.
41	COMP IN B	Comparator Inputs:
42	COMP IN A	From active differentiator output terminals, the read
		signals are differentially input to these terminals through
		AC coupling capacitor.
43	DIFF OUT A	Active Differentiator Output:
44	DIFF OUT B	From these terminal, the read signals are differentially
		input to the comparator input terminals thorugh the AC
		coupling capacitor.

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ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Power Supply Voltage (Pin 21)		VCC	17	V
Power Supply Voltage (Pin 35)		v_{DD}	7	V
Digital Input Voltage	(Note 1)	-	-0.5~5.5	V
Power On Detector Applied Voltage	(Note 2)	-	17	V
Erase Output Applied Voltage	(Note 3)	-	17	V
Head O/1 Applied Voltage	(Note 4)	-	17	V
Common Output Source Current		ICOM	75	mA
Erase Sink Current		IE	50	mA
Write Current		IW	25	mADC
Power On Sink Current	(Note 2)	-	7	mA
Operating Ambient Temperature Range		Ta	-20~75	°C
Operating Junction Temperature		Tj	150	°C
Storage Temperature		Tstg	-65~150	°C
Power Dissipation (Ta=25°C)	(Note 5)	PD	0.96	W

- (Note 1) These ratings apply to WRITE CURRENT, WRITE DATA, WRITE DATE, ERASE GATE SIDE 1, MMVA CONTROL, POWER SAVE, DDC1, 12V/5V SELECT.
- (Note 2) This rating applies to POWER ON (pin 32).
- (Note 3) This rating applies to ERASE OUTPUT (pin 24).
- (Note 4) These rating apply to (Pin 12)(Pin 13)(Pin 14)(Pin 15).
- (Note 5) In the actual operation refer to Fig.1.

TA8512AF

ELECTRICAL CHARACTERISTICS

(1) SUPPLY CURRENT I (Ta=25°C, V_{CC} =12V, V_{DD} =5V)

CHA	SYMBOL	FIGURE	MEASURE	CONDITION	MIN.	TYP.	MAX.	UNIT	
Read Mode	V _{DD} Supply Current	I _{DDR}	-				17.6	27.5	mA
Read Mode	VCC Supply Current	ICCR				-	7.2	8.6	mA
Write Mode	V _{DD} Supply Current	IDDW	-	IW=0		-	8.8	12.6	mA
write mode	V _{CC} Supply Current	ICCW	1-1			-	3.4	5.1	mA
Erase Mode	V _{DD} Supply Current	I _{DDE}	-			-	8.8	12.4	mA
Erase Mode	V _{CC} Supply Current	ICCE	-			-	3.6	5.6	mA
Write +	V _{DD} Supply Current	IDDW+E	-	IW=0		-	11.5	21.7	mA
Erase Mode	V _{CC} Supply Current	ICCW+E	-			-	3.3	5.3	mA
	V _{CC} Supply Current	IDDPS	-			-	1.3	2.7	mA
Power Save Mode	V _{CC} Supply Current	ICCPS	-			-	0.35	0.5	mA
riode	Total Power Dissipation	P _{DPS}	-			-	10.7	19.5	mW

SUPPLY CURRENT II (Ta=25°C, V_{CC}=5V, V_{DD}=5V)

DOLLER	CURRENT II (18-25	-, .00	, ,						
CHA	SYMBOL	FIGURE	MEASURE	CONDITION	MIN.	TYP.	MAX.	UNIT	
Read Mode	V _{DD} Supply Current	I _{DDR}	-			1-	17.7	23.4	mA
Read Mode	VCC Supply Current	ICCR	-			-	7.5	8.6	mA
Unita Mada	V _{DD} Supply Current	IDDW	-	IW=0		-	9.5	15.4	mA
Write Mode	V _{CC} Supply Current	ICCW	_			-	12.3	18.8	mA
E Mada	V _{DD} Supply Current	I _{DDE}	-			-	9.4	13.9	mA
Erase Mode	V _{CC} Supply Current	ICCE	-			-	12.6	19.2	mA
Write +	V _{DD} Supply Current	I _{DDW+E}	-	IW=0		-	12.3	19.4	mA
Erase Mode	V _{CC} Supply Current	ICCW+E	-			-	12.3	18.8	mA
	V _{DD} Supply Current	IDDPS	-			-	1.35	2.7	mA
Power Save Mode	V _{CC} Supply Current	ICCPS	-				0.27	0.4	mA
riode	Total Power Dissipation	P _{DPS}	-			-	8.1	15.5	mW

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INTEGRATED CIRCUIT TECHNICAL DATA

ELECTRICAL CHARACTERISTICS

(2) POWER SUPPLY MONITOR (Ta=25°C, V_{CC}=0~16V, V_{DD}=0~7V)

CHARACTERIS	TIC	SYMBOL	FIGURE	MEASURE CONDITION	MIN.	TYP.	MAX.	UNIT
5V Power Supply	Positive	V _T +	-		-	4.0 4.2		V
(VDD, VCC) Threshold Voltage	Negative	v _T -	-		3.6	4.0	-	
12V Power Supply Positive		VT+	-	V _{DD} =5V	_	9.0	10.0	V
(VCC) Threshold Voltage	Negative	v _T -	-	v DD-3v	8.2	9.0	_	
5V Power Supply Hy	steresis	V _T +-V _T -	-		_	150	-	mV
12V Power Supply F	lysteresis	V _T +-V _T -	-		300	-	-	mV
Power On Output (Pin 32) Saturated Voltage			-	V _{DD} =3.6V I _{SINK} =5mA	-	-	0.4	V
Power On Output (Pin 32) Leakage Current			-	V _{DD} > 4.5V	-	-	10	μА

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ELECTRICAL CHARACTERISTICS

(3) PRE AMPLIFIER. ACTIVE DIFFERENTIATOR. COMPARATOR (Ta=25°C, V_{CC} =12 V_{CS})

	CHARACTERISTIC	SYMBOL	FIGURE	MEASURE CONDITION	MIN.	TYP.	MAX.	UNIT
	Differential Voltage	G _{V1}	2	f=1MHz	170	200	230	v/v
Amplifier	Gain	G _V 2	2	f=1MHz	85	100	115	
Amp1	Bandwidth (-3dB)	BW	2		-	5	-	MHz
/Pre	Common Mode Rejection Ratio	CMRR	-	Input Sine Wave f=1MHz, 200mVrms	50	-	-	dB
Matrix/Pre	Power Supply Rejection Ratio	PSRR	-	Supperposed Sine Wave f=10MHz, 1Vp-p	70	-	-	dB
Head Ma	Differential Input Resistance	RIN	-	f=62.5~500kHz	-	10	-	k
Не	Differential Input Capacitance	c_{IN}	-	f=125kHz	-	-	-	pF
	Differential Input Voltage Linear Operation	VIN	-	Gain × 100 times	0.8	-	15	mVp-p
er	Differential Output Voltage Linear Operation	V _{OUT}	2		2.0	3.0	-	Vp-p
Amplifi	Differential Output Sink Current	IOUT	-		3.0	4.0	5.0	mAp-p
	Differential Output Off Set	Vofs	-		-	-	0.5	V
Pre	Noise Voltage Refered to Input	EN	2	Head Connected Terminals Short BW=400Hz~1MHz	-	4.0	6.0	μV _{rms}
or	Band Width (-3dB)	F _{CD}	7=		10	15	-	MHz
erentiator	Differential Output Voltage Linear Operation	V _{OUT D}	-		-	2	-	Vp-p
44	Differential Output Off Set	Vof D			-	20	-	mV
e Dif	Differential Input Resistance	RIN D	-		12	-	-	kΩ
Active	Differential Output Resistance	ROUT D	-		-	200	-	Ω
A	Sink Current (Pin 2,3,4)	ISINK D	-		1.4	2.0	-	mA
arator	Differential Input Voltage Linear Operation	V _{IN} C	-		-	2	-	Vp-p
Сотра	Differential Input Resistance	RIN C	-		12	-	-	kΩ

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ELECTRICAL CHARACTERISTICS

(4) TIME DOMAIN FILTER - DIGITAL OUTPUT (Ta=25°C, V_{CC} =12 V_{CS} -5 V_{DD} =5 V_{CS})

CHA	ARACTERISTIC	SYMBOL	FIGURE	MEASURE CONDITION	MIN.	TYP.	MAX.	UNIT
Timing Ran One-shot	nge of First	t1	3		200	-	3000	ns
Timing Ran One-shot	nge of Second	t2	3		100	-	1200	ns
R _{MMVA} Comp Saturated	p Connect (Pin 40) Voltage	V _{MMC}	-	I _{SINK} =10μA	-	-	50	mV
Timing Ac One-shot	curacy of First	E _{TM1}	3		-18	_	+18	%
Timing Ac One-shot	curacy of Second	E _{TM} 2	3		-20	-	+20	%
Corrected Timing Accuracy of First One-shot		E _{TM1} C	3		- 15	-	+15	%
Peak Shift		PS	3	Comparator Input Wave f=250kHz, Differential Input Level 200mVp-p	_	-	1	%
	Output Voltage Low Level	V _L OUT	-	I _{OL} =2mA	-	-	0.5	V
	Output Voltage			I _{OH} =-10μA	3.5	-	-	V
	High Level	V _H OUT	_	I _{OH} =-0.4mA	2.8	-	-	
Digital	Sink Current	ISIRD	-	V _{OUT} =0.8V	2	4	-	mA
Output (Pin 33)	Soure Current	ISORD	_	V _{OUT} =2.8V	0.4	1	-	mA
	Output Rise Time	tr		From 0.5~2.2V	-	-	25	
	Output Fall Time	tf	3	at 20pF Capacitance Load	-	-	25	ns

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ELECTRICAL CHARACTERISTICS

(5) WRITE DRIVER \cdot ERASE DRIVER (Ta=25°C, V_{CC}=12V~5V, V_{DD}=5V)

	C	CHARACTERISTIC	SYMBOL	FIGURE	MEASURE CONDITION	MIN.	TYP.	MAX.	UNIT
		out Voltage Level at Write 2 l	VWCMH12	-	$V_{CC}=12V$, $I_W=25$ mADC	10.8	-	-	V
Driver		out Voltage Level at Write 2 2	V _{WCMH5}	ş. —	$V_{CC}=5V$, $I_W=25mADC$	4.4	-	-	V
Common D		out Voltage Level at Write Mode	VWCML	-		-	-	0.2	V
Com		out Voltage n Level at Read Mode	V _{RCMH}	1-7		2.3	2.6	2.9	V
		out Voltage Level at Read Mode	V _{RCML}			-	-	0.2	V
	Outp	out Current Range	ICOM	-		-	-	75	mA
rer	(Pir	se Current Output n 24) urated Voltage	VER	-	I _E =50mA	-	0.2	0.5	V
ase Driver	(Pin	se Current Output n 24) kage Current	I _{LKER}	-		_	_	15	μΑ
Er	Eras	se Current Range	IE			-	-	50	mA
		te Current Range ngle)	IW	-		-	-	20	mADC
į,		rected Write Current ge (Single)	IWC			-	-	5	mADC
Driver	Wri	te Current Setting	EW	-		-8	-	+8	%
ite D		uracy	EWC	-		-10	-	+10	70
Wri	Wri	te Current Unbalance	DW	-		-	-	1	%
		Comp Connect (Pin 25) urated Voltage	VWC	-	I _{SOURCE} =0.5mA	-	50	300	mV
		Leakage Current	ILKW	-		-	-	10	μА
ect	n13, n15)	Saturated Voltage	VSAT	-		-	2	-	V
Conn	12,Pi 14,Pi	Differential Output Capacitance	C _{OUT}	-		_	23	-	pF
Head	(Pin12, Pin13, Pin14, Pin15)	Differential Output Resistance	ROUT	-	f=1MHz	-	280	-	kΩ
								12AF_	

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ELECTRICAL CHARACTERISTICS

(6) CONTROL LOGIC (Ta=25°C, V_{CC} =12V, V_{DD} =5V)

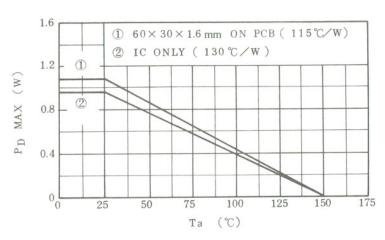
	CHARACTI	ERISTIC	SYMBOL	FIGURE	MEASURE	CONDITION	MIN.	TYP.	MAX.	UNIT
	Input Volta	age	$v_{ m LIN}$	-			-	-	0.8	V
Level	Input Volta High Level	age	VHIN	-			2.0	-	-	V
	Tilbut Tower SAVI		T	-	V _{IN} =0.4V		-	-	50	μА
Input	TICACT	Other Pins	I_{LIN}	-	V _{IN} =0.4V		-	-	250	μ21
T)	Input Current High Level (Pin 28,29,30,31)		I _{HIN1}	1 -	V _{IN} =2.4V		-	-	10	μА
Digi	Input Curre (Pin 27)	ent High Level	I _{HIN2}	-	V _{IN} =2.4V		-	-	130	μА
	Input Curr (Pin 34)	ent High Level	IHIN3	-	V _{IN} =2.4V		-	-	80	μА
	Negative Threshold		VLINS	-			0.8	1.0	-	V
e Dat	Voltage Positive Threshold Voltage		VHINS				-	1.6	2.0	V
Write	Hysteresis Hysteresis		V _{HINS} -	_			0.3	0.6	-	V

(7) AC SWITCHING CHARACTERISTICS (Ta=25°C, $V_{CC}=12V\sim5V$, $V_{DD}=5V$)

CHARACTERISTIC	MEASURE CONDITION	MIN.	TYP.	MAX.	UNIT
Dealy from PS Going High Through 2V to Read Mode	PS OFF→DIFF Output 90~110%	-	1	2	ms
Head Selecting Time		-	-	4	μs
Delay from WG Going High Through 2V to Read Mode	WG OFF → Select V _{COM} Voltage 90%	-	-	1	μѕ
WD-I _W Delay		-	-	0.3	μs
Write Current Rise Time 1	Lh=0mH	-	-	0.1	μs
Write Current Rise Time 2	Lh=1mH, $R_D=8.2k\Omega$, h=30pF	-	0.2	-	μs
Delay from EG Going High Through 2V to Read Mode	EG OFF→DIFF Output 90~110%	-	-	20	μs
Read Recovery Time	WG, EG OFF → DIFF Output 90%	-	30	40	μs
Power On Output Sink Current Rise or Fall Time (Pin 32)	Load (Pin 32) Ω 100kΩ (Pin 32) Ω 1μF	-	-	100	ms

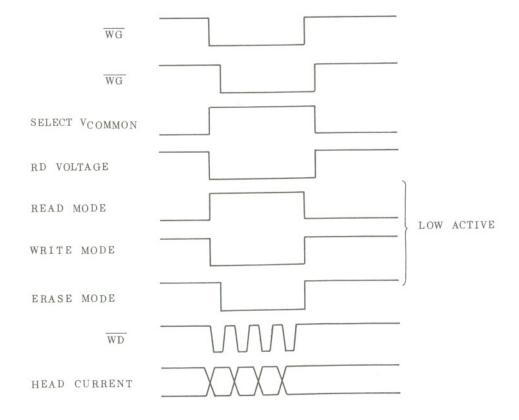
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The maximum of operating ambient temperature (Ta) of TA8512AF is 75° C, but the power dissipation (PD) differs according to the ambient temperature, so that in the actual operation refer to the above graph.

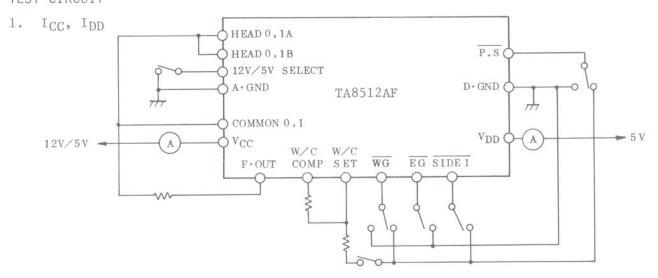
TIMING CHART

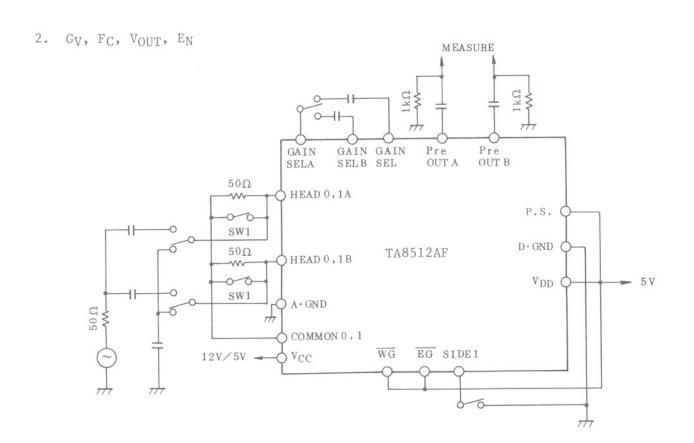


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INTEGRATED CIRCUIT

TEST CIRCUIT



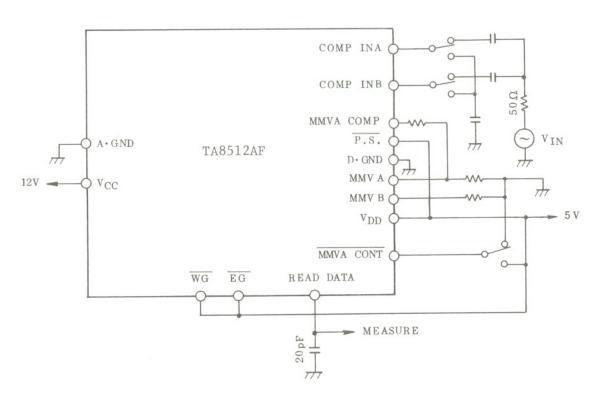


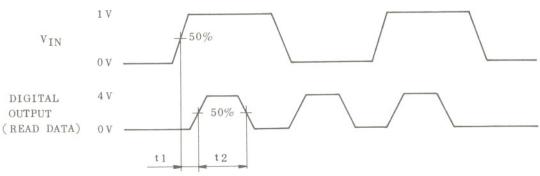
Note 1 : In the measurement of $G_{\rm V}$, $F_{\rm C}$ and $V_{\rm OUT}$, the input signal is applied to either selected one terminal of HEAD 0.1A or HEAD 0, 1B.

Note 2 : In measuring $\text{E}_{\rm N}$ only, SW1 is closed.

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3. t1, T2, EMT1, EMT2, EMTIC, PS, tr, tf





Fir.3-1 t1, t2

(1) Timing accuracy of frist and secound one-shot.

RMMVA and RMMVB which set the period (t1) of first one-shot to 1μ s, the period (t2) of secound to 0.5μ s connect and measure the digital output as above. ETM1, ETM2 are diffined as follows:

$$ETM1 = (1-t1/1) \times 100$$
 (%)

$$(t1[\mu s], t2[\mu s])$$

$$ETM2 = (0.5-t2/0.5) \times 100$$
 (%)

TA8512AF-17 1989-11-28 TOSHIBA CORPORATION (2) Corrected timing accuracy of first one-shot

RMMVA and RMMVA comp which set difference tl-tl' to 1µs connect.

(tl is the period of first one-shot when applies 2V to MMVA CONTROL, tl' is that one when applies 0.8V to MMVA CONTROL.)

EMTIC is difined as follow:

EMTIC =
$$[1 - (t1-t1')] \times 100$$
 (%)

(3) PEAK SHIFT

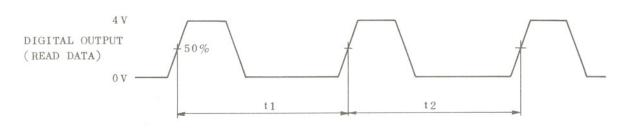
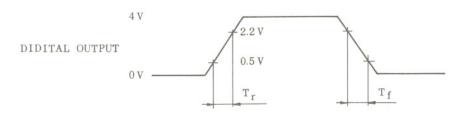


Fig. 3-2 P.S.

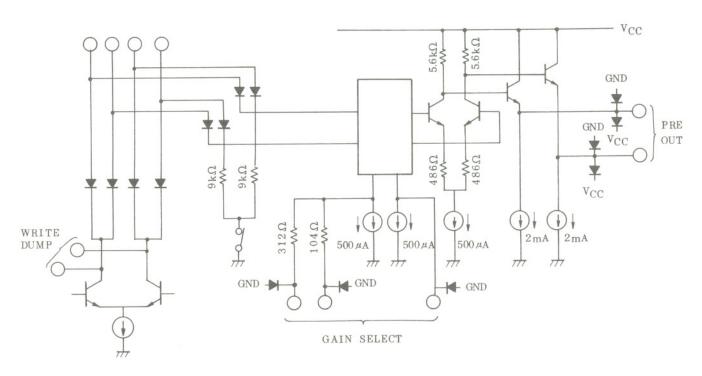
$$PS = \frac{1}{2} \times \frac{t1-t2}{t1+t2} \times 100$$
 (%)

(4) Digital Output (Read Data) Rise Time, Fall Time

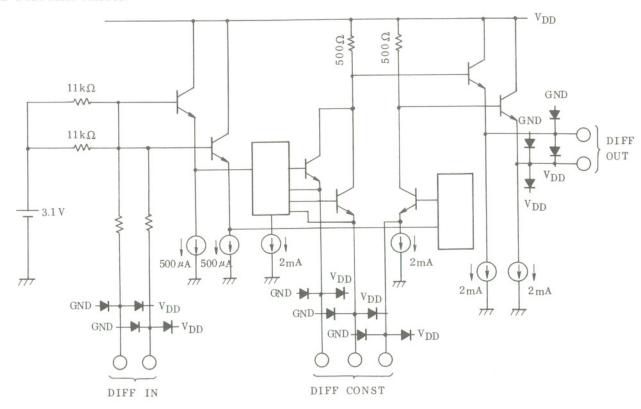


INTEGRATED CIRCUIT

PREAMPLIFIER



ACTIVE DIFFERENTIATOR

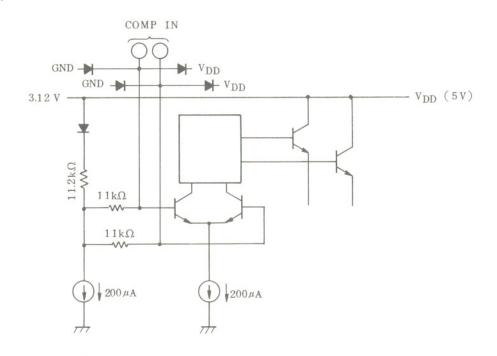


	TA8	512AF-19
	198	39-11-28
TOSH	HIBA	CORPORATION

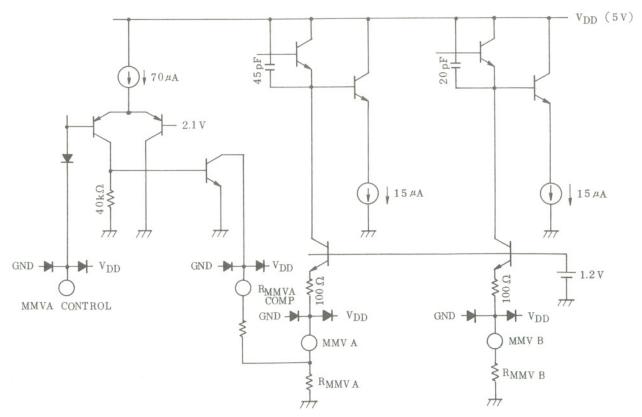


INTEGRATED CIRCUIT

COMPARATOR

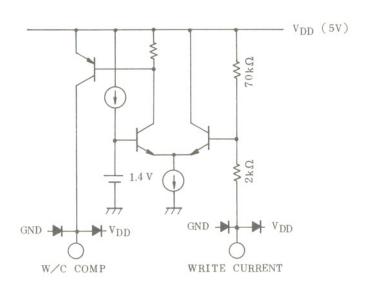


TIME DOMAIN FILTER

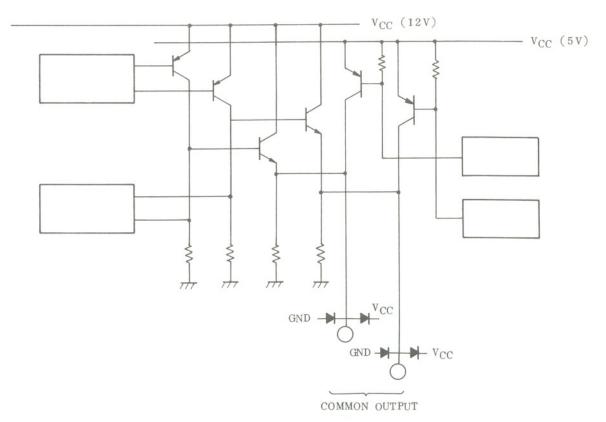


TA8512AF-20
1989-11-28
TOSHIBA CORPORATION

W/C CONTROL

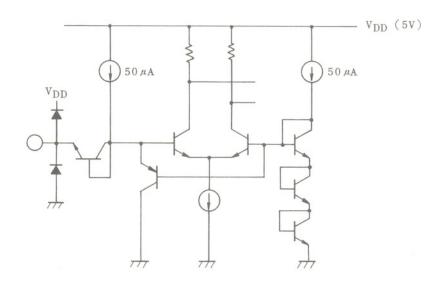


COMMON DRIVER OUTPUT

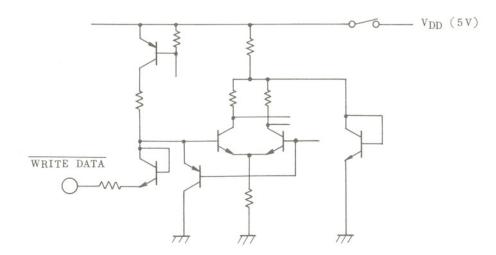


TA8512AF-21	
1989-11-28	

WRITE GATE, ERASE GATE, SIDE 1 INTERFACE



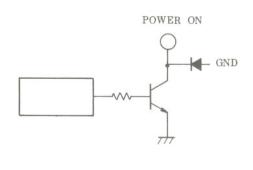
WRITE DATA INTERFACE

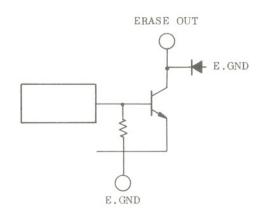


TA8.	512AF-22	
198	9-11-28	

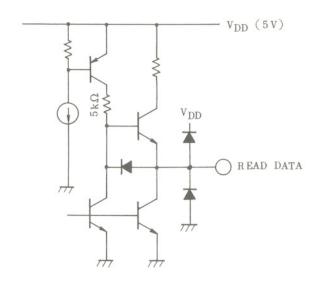
POWER SUPPLY VOLTAGE

ERASE OUTPUT



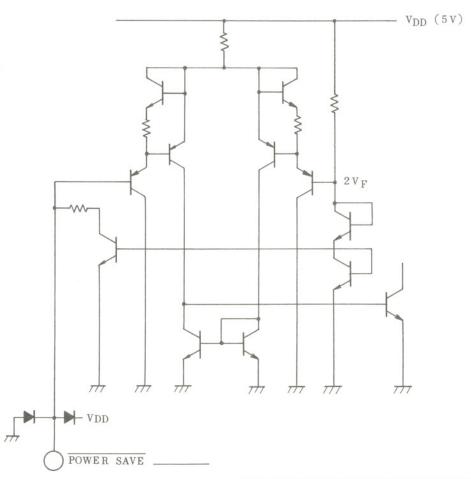


DIGITAL OUTPUT



TA8512AF-23 1989-11-28

POWER SAVE INTERFACE



INPUT VOLTAGE	POWER SAVE MODE
Н	In Active
L	Active
OPEN	Active

	TA8512AF-24 *	
	1989-11-28	
TO0:		